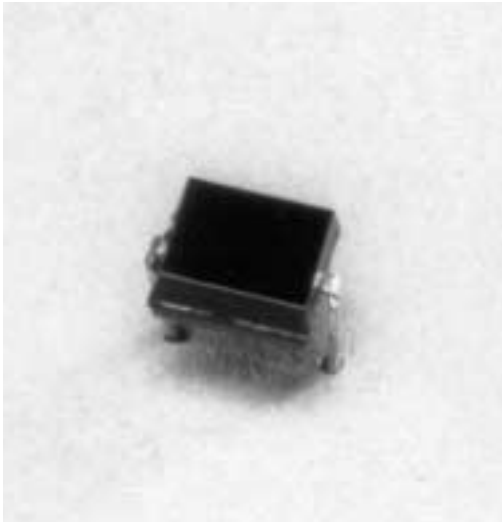
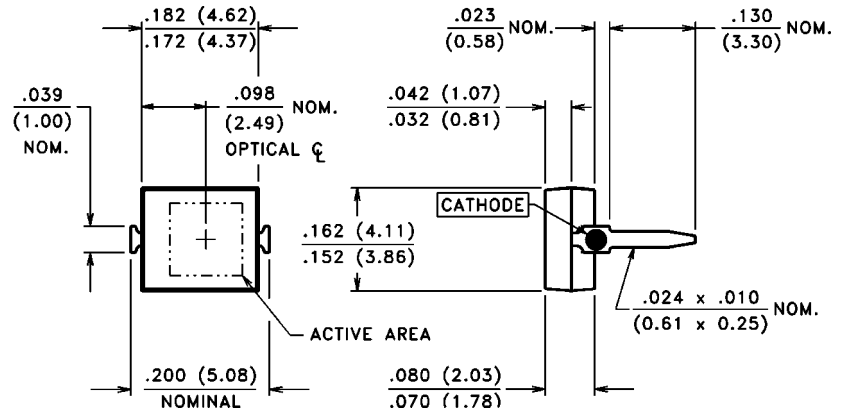


Alternate Source/ Second Source Photodiodes

VTD34FH (BPW34F INDUSTRY EQUIVALENT)



PACKAGE DIMENSIONS inch (mm)



CASE 22 MINI DIP
CHIP ACTIVE AREA: .012 in² (7.45 mm²)

PRODUCT DESCRIPTION

Planar silicon photodiode in a molded plastic package. The package material filters out visible light but passes infrared. Suitable for direct mounting to P.C.B. Arrays can be formed by positioning these devices side by side. The photodiodes are designed to provide excellent sensitivity at low levels of irradiance.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:

-20°C to 80°C

Operating Temperature:

-20°C to 80°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTD34FH			UNITS
			Min.	Typ.	Max.	
R_e	Responsivity	0.5 mW/cm ² , 940 nm	15			μA
V_{OC}	Open Circuit Voltage	0.5 mW/cm ² , 940 nm	275	350		mV
$TC V_{OC}$	V_{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I_D	Dark Current	H = 0, V_R = 10 V		2	30	nA
C_J	Junction Capacitance	@ 1 MHz, V_R = 0 V		60		pF
t_R/t_F	Rise/Fall Time @ 1 kΩ Lead	V_R = 10 V, 833 nm		50		nsec
S_R	Sensitivity	@ Peak		0.60		A/W
λ_{range}	Spectral Application Range		725		1150	nm
λ_p	Spectral Response - Peak			940		nm
V_{BR}	Breakdown Voltage		40			V
$\theta_{1/2}$	Angular Resp.-50% Resp. Pt.			±50		Degrees
NEP	Noise Equivalent Power			4.8×10^{-14}		W/√Hz
D^*	Specific Detectivity			5.7×10^{12}		cm√Hz/W

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nordics@amstechnologies.com
aspect.amstechnologies.com

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